

L Number	Hits	Search Text	DB	Time stamp
-	2919	"heterojunction bipolar transistor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 11:18
-	498500	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 10:16
-	308	"heterojunction bipolar transistor" and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 09:32
-	107261	resistive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 09:33
-	65	("heterojunction bipolar transistor" and capacitor) and resistive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 09:33
-	24	5268315.URPN.	USPAT	2002/06/12 09:38
-	5	("4691215" "4771013" "4981807" "5051372" "5166083").PN.	USPAT	2002/06/12 09:41
-	725	(257/197).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 10:13
-	29417	capacitor and resistive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 10:17
-	9	((257/197).CCLS.) and (capacitor and resistive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 10:17
-	984	(257/565).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:36
-	46	"heterojunction bipolar transistor" and ((257/565).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:37
-	490878	resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:37
-	11	("heterojunction bipolar transistor" and ((257/565).CCLS.)) and resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:52
-	0	"Irl W. Smith".in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:53

-	0	"heterojunction bipolar transistor" and compound adj resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:56
-	75	compound adj resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:57
-	2588	bjt or bipolarr adj junction adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:58
-	0	(compound adj resistor) and (bjt or bipolarr adj junction adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:58
-	42	resistor near (GaAS or InP or III-V)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:58
-	2	("6005267").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 18:19
-	3731	hbt	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:15
-	490878	resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:15
-	520492	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:16
-	0	hbt and "2" and "3"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:16
-	2070	hbt and "2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:16
-	835	hbt and resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:16
-	581	capacitor and (hbt and resistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:17
-	189315	semiconductor adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:18

-	232	(capacitor and (hbt and resistor)) and (semiconductor adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:18
-	207	electrode and ((capacitor and (hbt and resistor)) and (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:19
-	52733	bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:20
-	201	(electrode and ((capacitor and (hbt and resistor)) and (semiconductor adj substrate))) and (bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/30 10:20
-	29	5268315.URPN.	USPAT	2003/04/30 10:28
-	6	5559349.URPN.	USPAT	2003/04/30 10:32
-	2090	furuhata.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 07:22
-	23	emitter and capacitor and furuhata.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 07:38
-	108	(438/329).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 07:38
-	13	5336632.URPN.	USPAT	2003/09/01 07:49
-	3	(hetero adj junction or heterojunction) and bipolar adj transistor and (electrode near7 "same thickness")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 08:13
-	0	"heterojunction bipolar transistor" and (conformal near metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 08:36
-	82	"heterojunction bipolar transistor" and (conformal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 08:36
-	28	capacitor and ("heterojunction bipolar transistor" and (conformal))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 08:49
-	7	5223449.URPN.	USPAT	2003/09/01 08:47
-	824	hbt and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/01 11:18

-	92	(emitter adj electrode or base adj electrode or collector adj electrode) and (hbt and capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/01 09:29
-	1007	(257/565).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/01 11:18
-	4	hbt and capacitor and ((257/565).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/01 11:19
-	75	(257/576).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/01 11:25
-	857	(257/577).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/01 11:28
-	20	((257/565).CCLS.) and ((257/577).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/01 11:25
-	128	(257/584).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/01 11:28